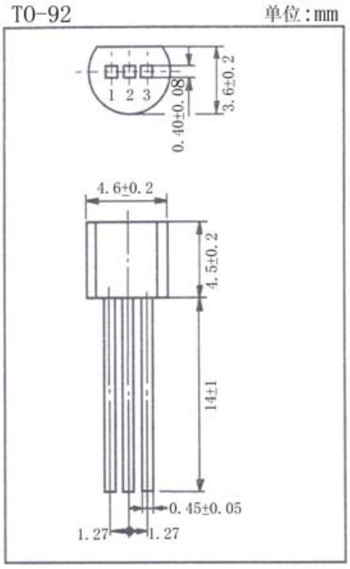
MJE13003J1G(3DD13003J1G) 硅NPN半导体三极管/SILICON NPN TRANSISTOR

用途：主要用于节能灯、日光灯电子镇流器及其它开关、振荡电路。

Purpose: High frequency electronic lighting ballast applications，converters, inverters, switching regulators, etc.

极限参数/Absolute maximum ratings(Ta=25℃)

参数符号 Symbol	数值 Rating	单位 Unit
V_{CBO}	900	V
V_{CEO}	550	V
V_{EBO}	9.0	V
I_C	1.5	A
I_{CP}	3.0	A
P_C(Ta=25℃)	1.0	W
T_j	150	℃
T_{stg}	-55～150	℃

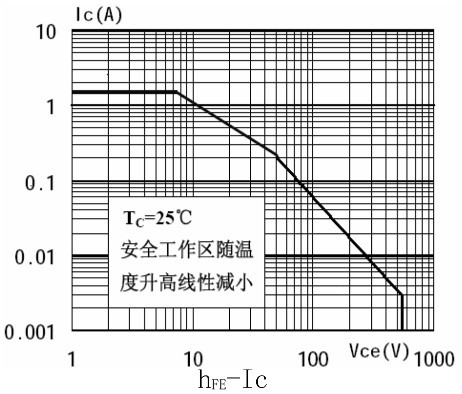


引脚:1.E 2.C 3.B

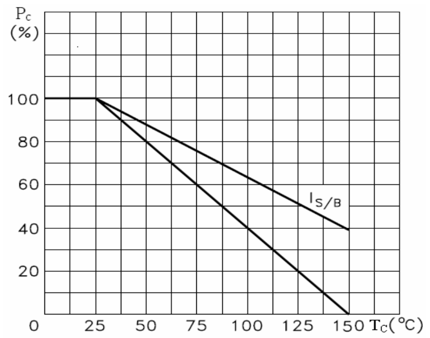
电性能参数/Electrical characteristics(Ta=25℃)

参数符号 Symbol	测试条件 Test condition	数值 Rating 最小值 Min	 典型值 Typ	 最大值 Max	单位 Unit
V_{CBO}	I_C=1mA I_E=0	900			V
V_{CEO}	I_C=10mA I_B=0	550			V
V_{EBO}	I_E=1mA I_C=0	9			V
I_{CBO}	V_{CB}=900V I_E=0			0.1	mA
I_{CEO}	V_{CE}=550V I_B=0			0.1	mA
I_{EBO}	V_{EB}=9.0V I_C=0			0.1	mA
$h_{FE(1)}$	V_{CE}=10V I_C=400mA	10		40	
$h_{FE(2)}$	V_{CE}=10V I_C=1.0mA	13			
$h_{FE(3)}$	V_{CE}=10V I_C=1.0A	6			
$V_{CE(sat)\ (1)}$	I_C=1A I_B=0.25A			1	V
$V_{CE(sat)\ (2)}$	I_C=1.5A I_B=0.5A			2.5	V
$V_{BE(sat)}$	I_C=1A I_B=0.25A			1.5	V
f_T	V_{CE}=10V I_C=0.1A f=1.0MHz	5.0			MHz
t_f	V_{CE}=5V I_C=0.25A (UI9600)			1.2	μs
t_S		2		6	μs

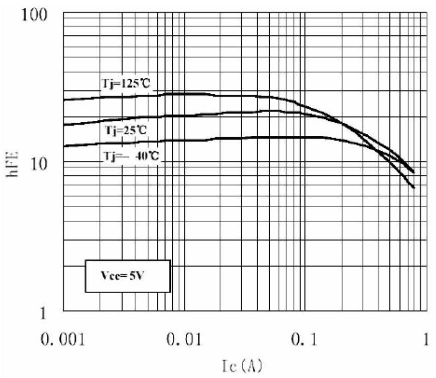
SOA(DC)



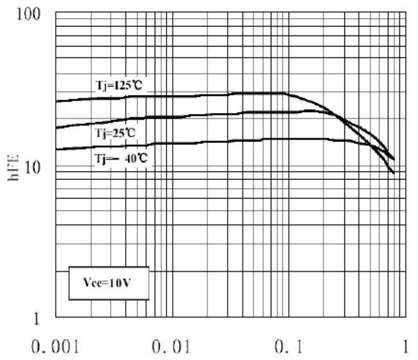
P_C-T_C



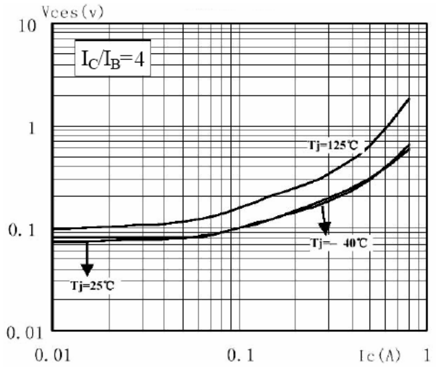
h_{FE}-Ic



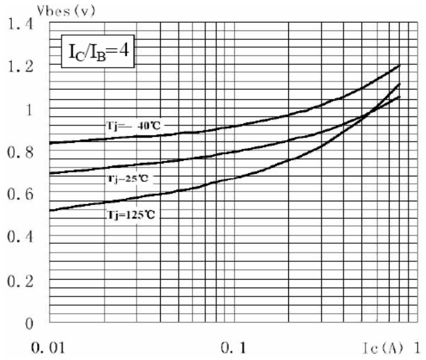
h_{FE}-Ic



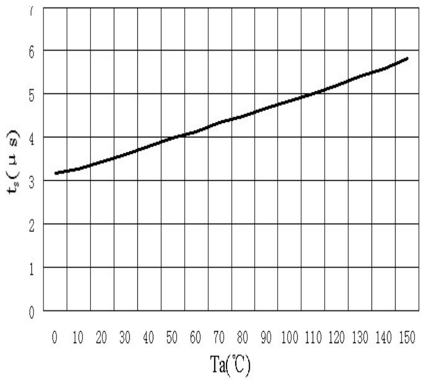
Vces-I_C



Vbes-I_C



t_S-Ta



h_{FE}-Ta